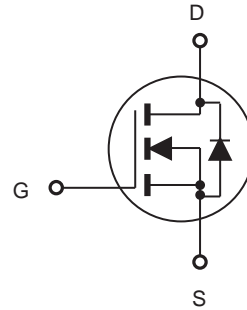
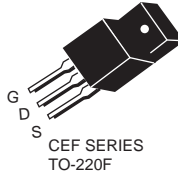


## N-Channel Enhancement Mode Field Effect Transistor

### FEATURES

Type	$V_{DSS}@T_{Jmax}$	$R_{DS(ON)}$	$I_D$	@ $V_{GS}$
CEP45N65	700V	70m $\Omega$	45A	10V
CEB45N65	700V	70m $\Omega$	45A	10V
CEF45N65	700V	70m $\Omega$	45A <sup>d</sup>	10V

- Super high dense cell design for extremely low  $R_{DS(ON)}$ .
- High power and current handling capability.
- RoHS compliant.



### ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Limit		Units
		TO-220/263	TO-220F	
Drain-Source Voltage	$V_{DS}$	650		V
Gate-Source Voltage	$V_{GS}$	$\pm 20$		V
Drain Current-Continuous @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	$I_D$	45	45 <sup>d</sup>	A
		28	28 <sup>d</sup>	A
Drain Current-Pulsed <sup>a</sup>	$I_{DM}^e$	180	180 <sup>d</sup>	A
Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ - Derate above $25^\circ\text{C}$	$P_D$	357	89	W
		2.86	0.71	W/ $^\circ\text{C}$
Single Pulsed Avalanche Energy <sup>g</sup>	$E_{AS}$	1200		mJ
Single Pulsed Avalanche Current <sup>g</sup>	$I_{AS}$	8		A
Operating and Store Temperature Range	$T_J, T_{stg}$	-55 to 150		$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Limit		Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.35	1.4	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	65	$^\circ\text{C}/\text{W}$



# CEP45N65/CEB45N65 CEF45N65

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	650			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 650V, V_{GS} = 0V$			1	$\mu A$
Gate Body Leakage Current, Forward	$I_{GSSF}$	$V_{GS} = 20V, V_{DS} = 0V$			100	nA
Gate Body Leakage Current, Reverse	$I_{GSSR}$	$V_{GS} = -20V, V_{DS} = 0V$			-100	nA
<b>On Characteristics<sup>b</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	2		4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$		58	70	m $\Omega$
<b>Dynamic Characteristics<sup>c</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 100V, V_{GS} = 0V,$ $f = 1.0 \text{ MHz}$		2500		pF
Output Capacitance	$C_{oss}$			170		pF
Reverse Transfer Capacitance	$C_{rss}$			5		pF
<b>Switching Characteristics<sup>c</sup></b>						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 520V, I_D = 10A,$ $V_{GS} = 10V, R_{GEN} = 10\Omega$		38		ns
Turn-On Rise Time	$t_r$			12		ns
Turn-Off Delay Time	$t_{d(off)}$			132		ns
Turn-Off Fall Time	$t_f$			6		ns
Total Gate Charge	$Q_g$	$V_{DS} = 520V, I_D = 10A,$ $V_{GS} = 10V$		77		nC
Gate-Source Charge	$Q_{gs}$			12		nC
Gate-Drain Charge	$Q_{gd}$			26		nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Drain-Source Diode Forward Current	$I_S^f$				45	A
Drain-Source Diode Forward Voltage <sup>b</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = 20A$			1.5	V
<b>Notes :</b> a.Repetitive Rating : Pulse width limited by maximum junction temperature . b.Pulse Test : Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 2\%$ . c.Guaranteed by design, not subject to production testing. d.Limited only by maximum temperature allowed . e.Pulse width limited by safe operating area . f.Full package $I_{S(max)} = 22A$ . g.L = 37.5mH, $I_{AS} = 8A, V_{DD} = 60V, R_G = 25\Omega$ , Starting $T_J = 25^\circ\text{C}$ .						

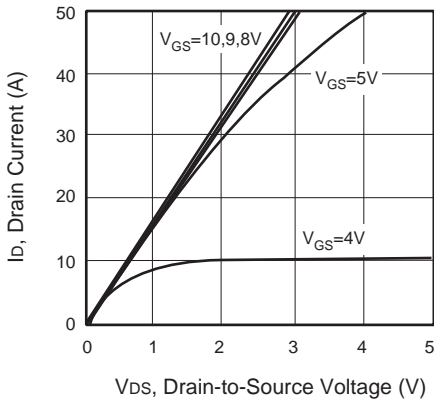


Figure 1. Output Characteristics

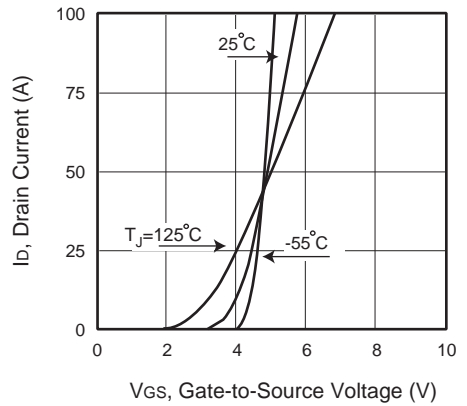


Figure 2. Transfer Characteristics

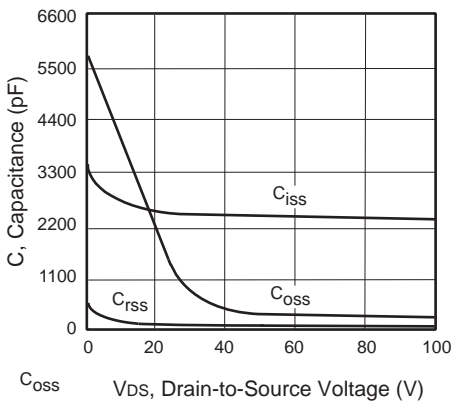


Figure 3. Capacitance

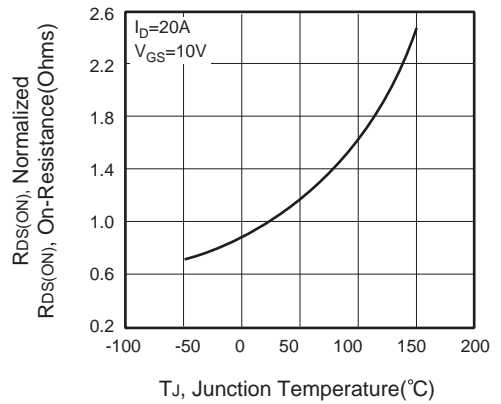


Figure 4. On-Resistance Variation with Temperature

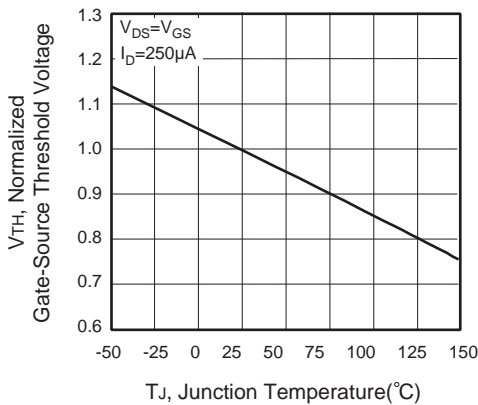


Figure 5. Gate Threshold Variation with Temperature

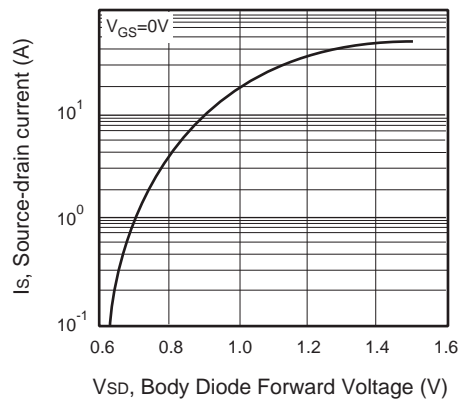


Figure 6. Body Diode Forward Voltage Variation with Source Current

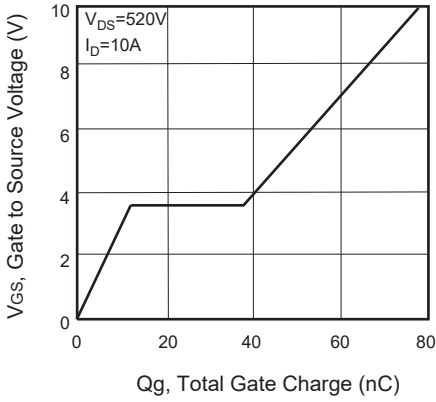


Figure 7. Gate Charge

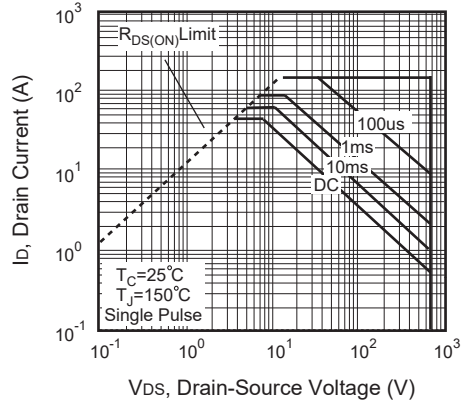


Figure 8. Maximum Safe Operating Area



Figure 9. Breakdown Voltage Variation VS Temperature



Figure 10. Switching Test Circuit

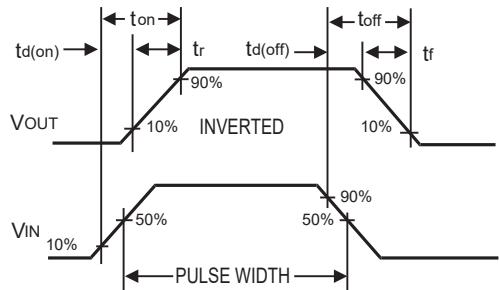
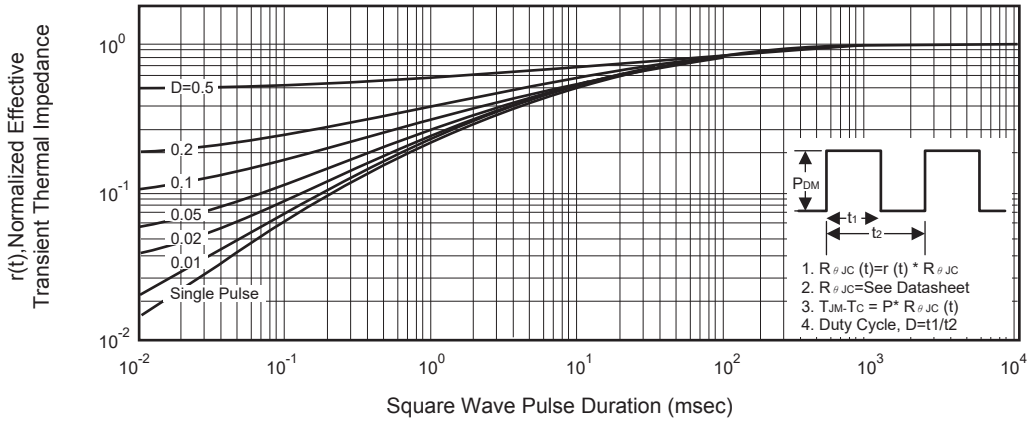


Figure 11. Switching Waveforms



**Figure 12. Normalized Thermal Transient Impedance Curve**